Marilena Vivona

List of Publications by Year
in descending order

52	768	687363 13	552781 26
papers	citations	h-index	g-index

52	52	52	662
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Electrical evolution of W and WC Schottky contacts on 4H-SiC at different annealing temperatures. Semiconductor Science and Technology, 2022, 37, 015012.	2.0	5
2	Temperature and time dependent electron trapping in Al2O3 thin films onto AlGaN/GaN heterostructures. Applied Surface Science, 2022, 579, 152136.	6.1	3
3	Materials and Processes for Schottky Contacts on Silicon Carbide. Materials, 2022, 15, 298.	2.9	8
4	Selective Doping in Silicon Carbide Power Devices. Materials, 2021, 14, 3923.	2.9	31
5	Ni Schottky barrier on heavily doped phosphorous implanted 4H-SiC. Journal Physics D: Applied Physics, 2021, 54, 445107.	2.8	12
6	Barrier height tuning in Ti/4H-SiC Schottky diodes. Solid-State Electronics, 2021, 186, 108042.	1.4	13
7	Electrical properties of inhomogeneous tungsten carbide Schottky barrier on 4H-SiC. Journal Physics D: Applied Physics, 2021, 54, 055101.	2.8	12
8	Active dopant profiling and Ohmic contacts behavior in degenerate n-type implanted silicon carbide. Applied Physics Letters, 2020, 117, .	3.3	8
9	Properties of Al2O3 thin films deposited on 4H-SiC by reactive ion sputtering. Materials Science in Semiconductor Processing, 2019, 93, 290-294.	4.0	10
10	Full non-destructive characterization of doped optical fibre preforms. , 2019, , .		0
11	Temperature-dependent Fowler-Nordheim electron barrier height in SiO2/4H-SiC MOS capacitors. Materials Science in Semiconductor Processing, 2018, 78, 38-42.	4.0	27
12	Instrumentation for Simultaneous Non-Destructive Profiling of Refractive Index and Rare-Earth-Ion Distributions in Optical Fiber Preforms. Instruments, 2018, 2, 23.	1.8	2
13	Non-destructive characterization of rare-earth-doped optical fiber preforms. Optics Letters, 2018, 43, 4907.	3.3	7
14	Non-destructive microscopic characterization of optical fiber preforms. , 2018, , .		0
15	Properties of SiO₂/4H-SiC Interfaces with an Oxide Deposited by a High-Temperature Process. Materials Science Forum, 2017, 897, 331-334.	0.3	2
16	Electrical and structural properties of surfaces and interfaces in Ti/Al/Ni Ohmic contacts to p-type implanted 4H-SiC. Applied Surface Science, 2017, 420, 331-335.	6.1	30
17	Ti/Al-based contacts to p-type SiC and GaN for power device applications. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600357.	1.8	17
18	Electrical characterization of trapping phenomena at SiO2 /SiC and SiO2 /GaN in MOS-based devices. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600366.	1.8	5

#	Article	IF	Citations
19	Radiation hardening of rare-earth doped fiber amplifiers. , 2017, , .		0
20	Near interface traps in SiO2/4H-SiC metal-oxide-semiconductor field effect transistors monitored by temperature dependent gate current transient measurements. Applied Physics Letters, 2016, 109, .	3.3	31
21	Effect of germanium doping on electrical properties of n-type 4H-SiC homoepitaxial layers grown by chemical vapor deposition. Journal of Applied Physics, 2016, 120, .	2.5	6
22	X-Ray Irradiation on 4H-SiC MOS Capacitors Processed under Different Annealing Conditions. Materials Science Forum, 2016, 858, 659-662.	0.3	2
23	Electrical properties of SiO2/SiC interfaces on 2Â°-off axis 4H-SiC epilayers. Applied Surface Science, 2016, 364, 892-895.	6.1	5
24	Ti/Al/W Ohmic contacts to p-type implanted 4H-SiC. Journal of Applied Physics, 2015, 118, .	2.5	27
25	Preliminary Study on the Effect of Micrometric Ge-Droplets on the Characteristics of Ni/4H-SiC Schottky Contacts. Materials Science Forum, 2015, 821-823, 424-427.	0.3	0
26	Nanoscale reliability aspects of insulator onto wide band gap compounds. , 2014, , .		0
27	Ge Mediated Surface Preparation for Twin Free 3C-SiC Nucleation and Growth on Low Off-Axis 4H-SiC Substrate. ECS Journal of Solid State Science and Technology, 2014, 3, P285-P292.	1.8	10
28	Ge Assisted 3C-SiC Nucleation and Growth by Vapour Phase Epitaxy on On-Axis 4H-SiC Substrate. Materials Science Forum, 2014, 806, 27-31.	0.3	0
29	Recent advances on dielectrics technology for SiC and GaN power devices. Applied Surface Science, 2014, 301, 9-18.	6.1	130
30	Comparative study of gate oxide in 4H-SiC lateral MOSFETs subjected to post-deposition-annealing in N2O and POCl3. Applied Physics A: Materials Science and Processing, 2014, 115, 333-339.	2.3	35
31	Thermal stability of the current transport mechanisms in Ni-based Ohmic contacts on n- and p-implanted 4H-SiC. Semiconductor Science and Technology, 2014, 29, 075018.	2.0	45
32	Design of Radiation-Hardened Rare-Earth Doped Amplifiers Through a Coupled Experiment/Simulation Approach. Journal of Lightwave Technology, 2013, 31, 1247-1254.	4.6	32
33	SiO2/4H-SiC interface doping during post-deposition-annealing of the oxide in N2O or POCl3. Applied Physics Letters, 2013, 103, .	3.3	70
34	Radiation hardening techniques for Er/Yb doped optical fibers and amplifiers for space application. Optics Express, 2012, 20, 8457.	3.4	99
35	Influence of ${m Ce}^{3+}$ Codoping on the Photoluminescence Excitation Channels of Phosphosilicate Yb/Er-Doped Glasses. IEEE Photonics Technology Letters, 2012, 24, 509-511.	2.5	14
36	Radiation hardening techniques for rare-earth-based optical fibers and amplifiers. Proceedings of SPIE, 2012, , .	0.8	4

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37	Coupled experiment/simulation approach for the design of radiation-hardened rare-earth doped optical fibers and amplifiers. , 2011, , .		2
38	Influence of Ce codoping and H2 pre-loading on Er/Yb-doped fiber: Radiation response characterized by Confocal Micro-Luminescence. Journal of Non-Crystalline Solids, 2011, 357, 1963-1965.	3.1	14
39	Radiation effects on fiber amplifiers: design of radiation tolerant Yb/Er-based devices. , 2011, , .		3
40	X-ray irradiation influence on prototype Er3+-optical fibers: confocal luminescence study. , 2010, , .		0
41	Radiation effects on rare-earth doped optical fibers. Proceedings of SPIE, 2010, , .	0.8	7
42	Probing at Nanoscale Underneath the Gate Oxides in 4H-SiC MOS-Based Devices Annealed in N₂O and POCl₃. Materials Science Forum, 0, 806, 143-147.	0.3	0
43	Electrical Characteristics of Schottky Contacts on Ge-Doped 4H-SiC. Materials Science Forum, 0, 778-780, 706-709.	0.3	11
44	Characterization of SiO₂/SiC Interfaces Annealed in N₂O or POCl₃. Materials Science Forum, 0, 778-780, 623-626.	0.3	10
45	Comparative Study of the Current Transport Mechanisms in Ni₂Si Ohmic Contacts on n- and p-Type Implanted 4H-SiC. Materials Science Forum, 0, 778-780, 665-668.	0.3	3
46	Evolution of the Electrical and Structural Properties of Ti/Al/W Contacts to p-Type Implanted 4H-SiC upon Thermal Annealing. Materials Science Forum, 0, 821-823, 428-431.	0.3	0
47	Processing and Characterization of MOS Capacitors Fabricated on 2Â°-Off Axis 4H-SiC Epilayers. Materials Science Forum, 0, 858, 663-666.	0.3	0
48	Anomalous Fowler-Nordheim Tunneling through SiO₂/4H-SiC Barrier Investigated by Temperature and Time Dependent Gate Current Measurements. Materials Science Forum, 0, 897, 123-126.	0.3	0
49	Metal/Semiconductor Contacts to Silicon Carbide: Physics and Technology. Materials Science Forum, 0, 924, 339-344.	0.3	12
50	Study of Ti/Al/Ni Ohmic Contacts to p-Type Implanted 4H-SiC. Materials Science Forum, 0, 924, 377-380.	0.3	3
51	Temperature-Dependence Study of the Gate Current SiO₂/4H-SiC MOS Capacitors. Materials Science Forum, 0, 924, 473-476.	0.3	1
52	Ni/Heavily-Doped 4H-SiC Schottky Contacts. Materials Science Forum, 0, 1062, 411-416.	0.3	0